

2SD2184

Silicon NPN epitaxial planar type

For low-frequency output amplification

■ Features

- High collector-emitter voltage (Base open) V_{CEO}
- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Allowing supply with the radial taping

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|---------------------------------------|-----------|-------------|------------------|
| Collector-base voltage (Emitter open) | V_{CBO} | 150 | V |
| Collector-emitter voltage (Base open) | V_{CEO} | 150 | V |
| Emitter-base voltage (Collector open) | V_{EBO} | 5 | V |
| Collector current | I_C | 1 | A |
| Peak collector current | I_{CP} | 1.5 | A |
| Collector power dissipation * | P_C | 1 | W |
| Junction temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |

Note) *: Printed circuit board: Copper foil area of 1 cm² or more, and the board thickness of 1.7 mm for the collector portion

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

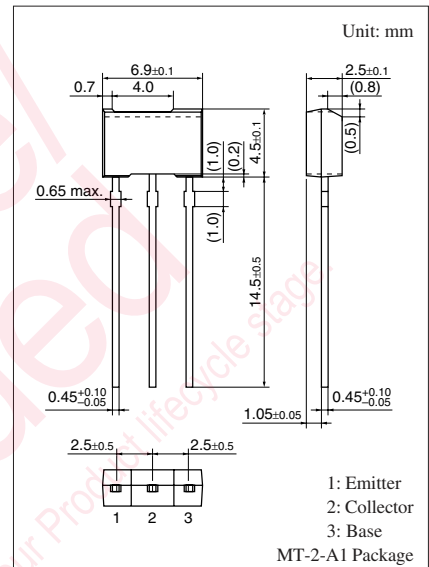
| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|---|----------------|--|-----|------|------|---------------|
| Collector-base voltage (Emitter open) | V_{CBO} | $I_C = 10 \mu\text{A}, I_E = 0$ | 150 | | | V |
| Collector-emitter voltage (Base open) | V_{CEO} | $I_C = 1 \text{ mA}, I_B = 0$ | 150 | | | V |
| Emitter-base voltage (Collector open) | V_{EBO} | $I_E = 10 \mu\text{A}, I_C = 0$ | 5 | | | V |
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{CB} = 75 \text{ V}, I_E = 0$ | | | 0.1 | μA |
| Forward current transfer ratio | h_{FE1}^{*2} | $V_{CE} = 2 \text{ V}, I_C = 100 \text{ mA}$ | 120 | | 340 | — |
| | h_{FE2}^{*1} | $V_{CE} = 2 \text{ V}, I_C = 500 \text{ mA}$ | 40 | | | |
| Collector-emitter saturation voltage ^{*1} | $V_{CE(sat)}$ | $I_C = 500 \text{ mA}, I_B = 25 \text{ mA}$ | | 0.11 | 0.30 | V |
| Base-emitter saturation voltage ^{*1} | $V_{BE(sat)}$ | $I_C = 500 \text{ mA}, I_B = 25 \text{ mA}$ | | 0.8 | 1.2 | V |
| Transition frequency | f_T | $V_{CB} = 10 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$ | | 90 | | MHz |
| Collector output capacitance (Common base, input open circuited) | C_{ob} | $V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ | | 12 | 20 | pF |

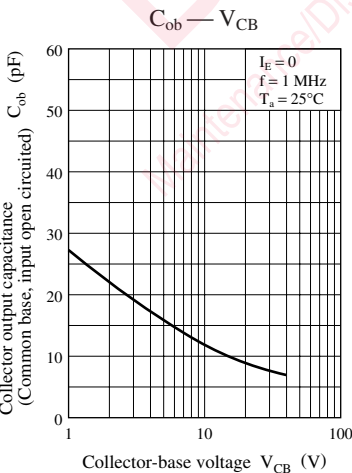
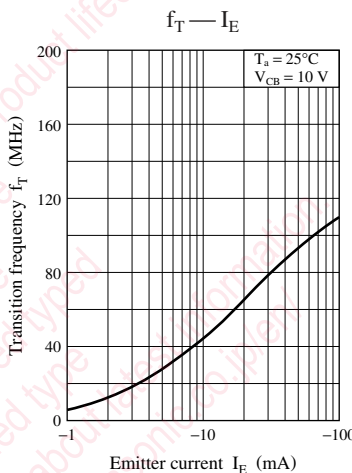
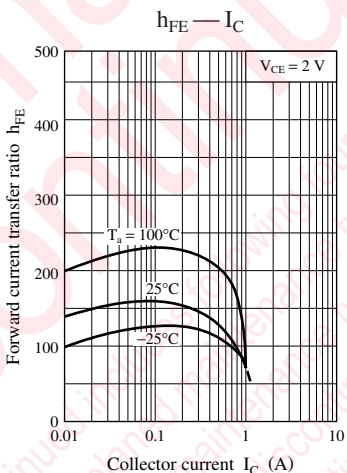
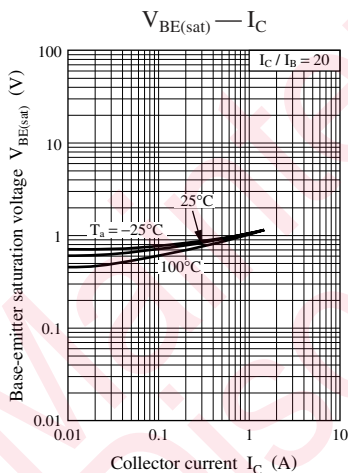
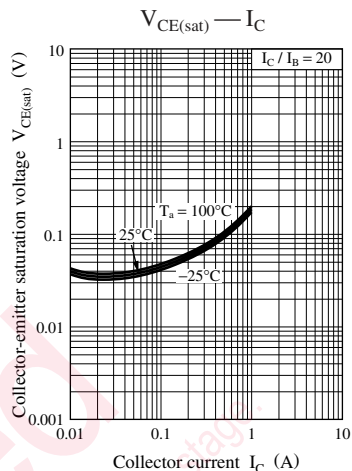
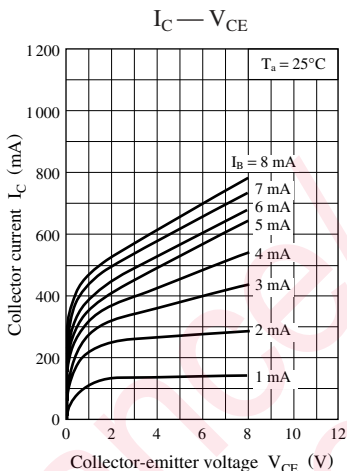
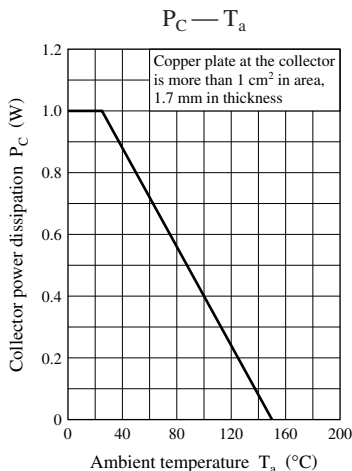
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement

*2: Rank classification

| Rank | R | S |
|-----------|------------|------------|
| h_{FE1} | 120 to 240 | 170 to 340 |





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